

PROCEEDINGS OF SPIE

Novel In-Plane Semiconductor Lasers XXI

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Editors

22–27 January 2022
San Francisco, California, United States

20–24 February 2022
ONLINE

Sponsored and Published by
SPIE

Volume 12021

Proceedings of SPIE 0277-786X, V. 12021

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Novel In-Plane Semiconductor Lasers XXI, edited by Alexey A. Belyanin,
Peter M. Snowton, Proc. of SPIE Vol. 12021, 1202101
© 2022 SPIE · 0277-786X · doi: 10.1117/12.2635256

Proc. of SPIE Vol. 12021 1202101-1

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Author(s), "Title of Paper," in *Novel In-Plane Semiconductor Lasers XXI*, edited by Alexey A. Belyanin, Peter M. Smowton, Proc. of SPIE 12021, Seven-digit Article CID Number (DD/MM/YYYY); (DOI URL).

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510649132

ISBN: 9781510649149 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time)

SPIE.org

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Contents

v *Conference Committee*

DFB AND DBRS

- 12021 02 **Full-C-band high-speed high-reliability wavelength switching at tunable DFB laser array with current/temperature cooperative control** [12021-1]
- 12021 03 **Electrically wavelength adjustable DBR laser for background-free Raman spectroscopy at 785 nm** [12021-3]
- 12021 04 **Slotted Y-branch laser for cw-THz thickness measurements at 1 THz** [12021-6]

MATERIALS AND STRUCTURE DEVELOPMENT

- 12021 05 **Investigation of deep level defects in n-type GaAsBi** [12021-10]
- 12021 06 **Integrated multi-wavelength DFB laser with 200 GHz channel spacing** [12021-51]

LASERS FOR INTEGRATION

- 12021 07 **Towards fully monolithic silicon-based integrated photonics: MOCVD grown lasers on silicon by blanket and selective area heteroepitaxy (Invited Paper)** [12021-18]
- 12021 08 **Optical degradation of InAs quantum-dot lasers on silicon: dependence on temperature and on diffusion processes** [12021-19]
- 12021 09 **Stability of a III-V/Si hybrid laser with a frequency-selective SiN mirror** [12021-20]
- 12021 0A **Control strategy for a monolithically integrated widely tunable laser system on InP for optical coherence tomography** [12021-21]

MID-IR LASERS AND INTEGRATED SYSTEMS

- 12021 0B **Electrically pumped epitaxially regrown $\lambda > 2 \mu\text{m}$ GaSb-based photonic crystal surface-emitting lasers (Invited Paper)** [12021-30]

Mid-IR QCLs: Modeling and New Architectures

- 12021 0C **Evaluation and analysis of operating characteristics for mid-infrared surface-emitting quantum cascade lasers** [12021-41]

MID-IR QCLS AND APPLICATIONS

- 12021 0D **High-definition video broadcasting with a room-temperature quantum cascade laser emitting in the long-wave infrared domain** [12021-46]
- 12021 0E **Quartz-enhanced photoacoustic spectroscopy employing a Vernier-effect distributed feedback-quantum cascade laser for multiple analytes detection** [12021-47]

HIGH BRIGHTNESS

- 12021 0F **Longitudinal spatial hole burning and associated non-uniform current and carrier density profile as a power limit in high power diode lasers (Invited Paper)** [12021-35]
- 12021 0G **Investigation of astigmatism in tapered edge-emitting diode amplifiers at 980 nm** [12021-37]
- 12021 0H **Comparison of electro-optical, spectral, and spatial beam parameters of 785 nm DBR tapered lasers with different grating lengths** [12021-38]

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